**Product data sheet** 

# 1. General description

Dual common cathode power Schottky diode in TO252 (DPAK) plastic package.





## 2. Features and benefits

- High junction temperature up to 175 °C
- Low forward voltage drop, negligible switching losses
- High efficiency

# 3. Applications

- · DC to DC converters
- Freewheeling diode
- OR-ing diode
- Switched mode power supply rectifier

## 4. Quick reference data

### Table 1. Quick reference data

| Symbol         | Parameter                       | Conditions  | Notes |     |      | Unit |    |  |  |  |  |
|----------------|---------------------------------|---|-------|-----|------|------|----|--|--|--|--|
| Absolute       | Absolute maximum rating         |   |       |     |      |      |    |  |  |  |  |
| $V_{RRM}$      | repetitive peak reverse voltage |   |       |     | 200  |      | V  |  |  |  |  |
| $I_{F(AV)}$    | average forward current         | $δ$ = 0.5 ; square-wave pulse; $T_{mb}$ ≤ 160 °C; per diode; Fig. 1; Fig. 2; Fig. 3 |       | 5   |      |      | А  |  |  |  |  |
| $I_{O(AV)}$    | average output current          | $\delta$ = 0.5 ; square-wave pulse; $T_{mb} \le 159$ °C; both diodes conducting     |       | 10  |      |      | А  |  |  |  |  |
| Symbol         | Parameter                       | Conditions  | Notes | Min | Max  | Unit |    |  |  |  |  |
| Static ch      | Static characteristics          |   |       |     |      |      |    |  |  |  |  |
| $V_{F}$        | forward voltage                 | $I_F = 5 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; per diode; Fig. 6                     |       | -   | 0.83 | 0.93 | V  |  |  |  |  |
| I <sub>R</sub> | reverse current                 | $V_R = 200 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; per diode;<br>Fig. 7; Fig. 8        |       | -   | 0.03 | 5    | μΑ |  |  |  |  |

# 5. Pinning information

**Table 2. Pinning information** 

| Pin | Symbol | Description                         | Simplified outline | Graphic symbol     |
|-----|--------|-------------------------------------|--------------------|--------------------|
| 1   | A1     | anode 1                             |                    |                    |
| 2   | K      | cathode                             |                    | A1 A2              |
| 3   | A2     | anode 2                             |                    | ———<br>К<br>sym125 |
| mb  | К      | mounting base; connected to cathode |                    | Symiles            |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number   | Package name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|---------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| WN3S10S200CDT | TO252        | WN3S10S200CDTJ        | Reel           | 2500                   | TO252d          | 07-Sep-2022        |

# 7. Marking

### **Table 4. Marking codes**

| Type number   | Marking codes     |
|---------------|-------------------|
| WN3S10S200CDT | WN3S10S<br>200CDT |

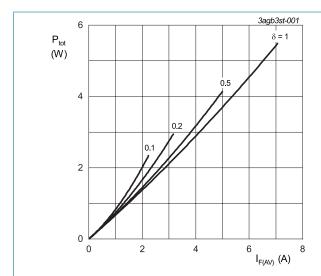
# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

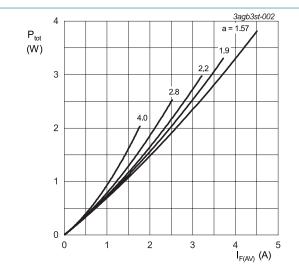
| Symbol           | Parameter                           | Conditions   | Notes | Values     | Unit |
|------------------|-------------------------------------|--|-------|------------|------|
| $V_{RRM}$        | repetitive peak reverse voltage     |  |       | 200        | V    |
| $V_{\text{RWM}}$ | crest working reverse voltage       |  |       | 200        | V    |
| $V_R$            | reverse voltage                     | DC   |       | 200        | V    |
| $I_{F(AV)}$      | average forward current             | $\delta$ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 160 °C; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u> |       | 5          | A    |
| $I_{O(AV)}$      | average output current              | $\delta$ = 0.5; square-wave pulse; $T_{mb} \le 159$ °C; both diodes conducting   |       | 10         | А    |
| I <sub>FSM</sub> | non-repetitive peak forward current | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4   |       | 130        | А    |
|                  |                                     | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode  |       | 143        | А    |
| T <sub>stg</sub> | storage temperature                 |  |       | -40 to 175 | °C   |
| T <sub>j</sub>   | junction temperature                |  | [1]   | -40 to 175 | °C   |

[1] The heat generated must be less than the thermal conductivity from Junction to Ambient:  $dP_{tot}/dT_j < 1/R_{th(j-a)}$ 



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ V<sub>o</sub> = 0.651 V; R<sub>s</sub> = 0.0177 Ω

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor =  $I_{F(RMS)}$  /  $I_{F(AV)}$  V<sub>o</sub> = 0.651 V;  $R_s$  = 0.0177  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

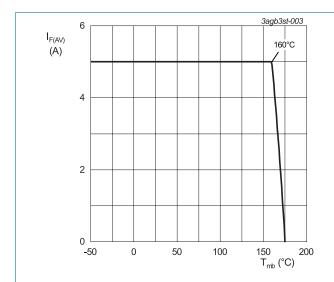


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

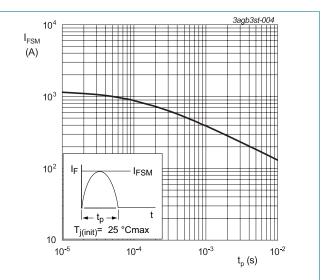


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

# 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter  | Conditions             | Notes | Min | Тур | Max | Unit |
|-----------------------|--|------------------------|-------|-----|-----|-----|------|
| $R_{\text{th(j-mb)}}$ | thermal resistance   | per diode; Fig. 5      |       | -   | -   | 3.7 | K/W  |
|                       | from junction to mounting base                             | both diodes conducting |       | -   | -   | 1.9 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient free air | in free air            |       | -   | 50  | -   | K/W  |

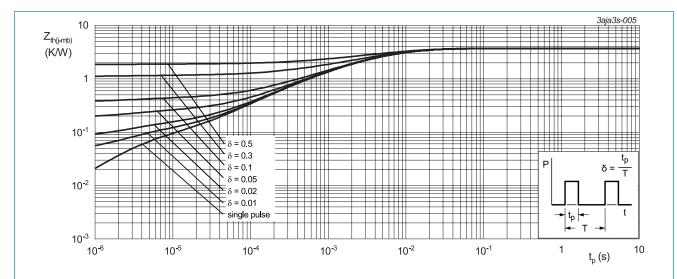
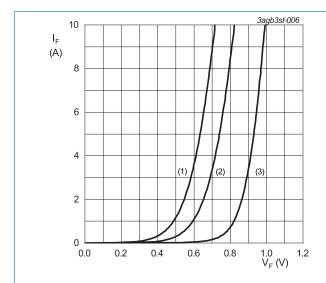


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

## 10. Characteristics

**Table 7. Characteristics** 

| Symbol                         | Parameter       | Conditions   | Notes | Min | Тур  | Max  | Unit |
|--------------------------------|-----------------|--|-------|-----|------|------|------|
| Static cha                     | aracteristics   |  |       |     |      |      |      |
| $V_{F}$                        | forward voltage | $I_F = 5 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; per diode; Fig. 6                          |       | -   | 0.83 | 0.93 | V    |
|                                |                 | I <sub>F</sub> = 5 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>                  |       | -   | 0.70 | -    | V    |
| I <sub>R</sub> reverse current |                 | $V_R = 200 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}; $<br>Fig. 7; Fig. 8  |       | -   | 0.03 | 5    | μA   |
|                                |                 | $V_R = 200 \text{ V}; T_j = 125 ^{\circ}\text{C}; \text{ per diode}; $<br>Fig. 7; Fig. 8 |       | -   | 0.4  | -    | mA   |



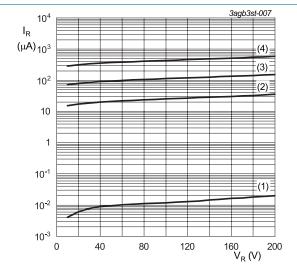
 $V_o = 0.651 \text{ V}; R_s = 0.0177 \Omega$ 

(1) T<sub>i</sub> = 175 °C; typical values

(2) T<sub>j</sub> = 175 °C; maximum values

(3)  $T_i = 25$  °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode



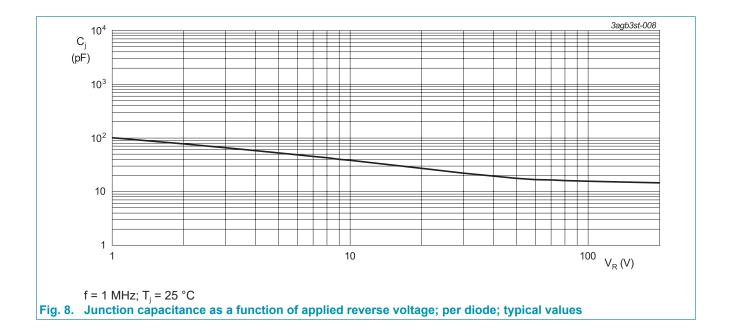
(1) T<sub>i</sub> = 25 °C; typical values

(2) T<sub>i</sub> = 125 °C; typical values

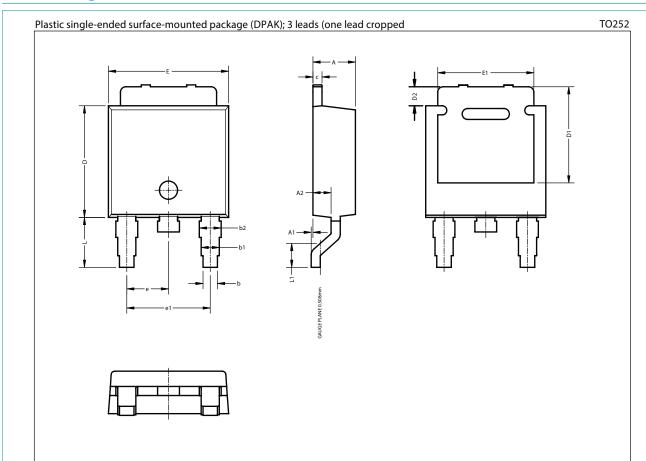
(3)  $T_i = 150 \,^{\circ}\text{C}$ ; typical values

(4) T<sub>i</sub> = 175 °C; typical values

Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values



# 11. Package outline



### Note:

1. All dimensions do not include mold flash & gate remain and metal protrusion.

| Unit | t          | Α    | A1   | <b>A</b> 2 | b    | b1   | b2   | С    | D    | D1   | D2   | E    | E1   | е    | e1   | L    | L1   |
|------|------------|------|------|------------|------|------|------|------|------|------|------|------|------|------|------|------|------|
|      | min<br>nom | 2.16 | 0.00 | 0.90       | 0.70 | 0.86 | 1.06 | 0.46 | 5.97 | 5.05 | 0.98 | 6.45 | 5.20 | 2.30 | 4.60 | 2.60 | 1.25 |
|      |            | 2.41 | 0.10 | 1.10       | 0.90 | 1.11 | 1.32 | 0.58 | 6.22 | 5.35 | 1.18 | 6.75 | 5.40 |      |      | 2.90 | 1.65 |

## 12. Legal information

#### Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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